

# FRL130D, FRL130R, FRL130H

8A, 100V, 0.180 Ohm, Rad Hard,  
N-Channel Power MOSFETs

June 1998

## Features

- 8A, 100V, RDS(on) = 0.180Ω
- Second Generation Rad Hard MOSFET Results From New Design Concepts
- Gamma
  - Meets Pre-Rad Specifications to 100KRAD(Si)
  - Defined End Point Specs at 300KRAD(Si) and 1000KRAD(Si)
  - Performance Permits Limited Use to 3000KRAD(Si)
- Gamma Dot
  - Survives 3E9RAD(Si)/sec at 80% BVDS Typically
  - Survives 2E12 Typically If Current Limited to IDM
- Photo Current
  - 1.5nA Per-RAD(Si)/sec Typically
- Neutron
  - Pre-RAD Specifications for 3E13 Neutrons/cm<sup>2</sup>
  - Usable to 3E14 Neutrons/cm<sup>2</sup>

## Description

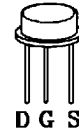
The Harris Semiconductor Sector has designed a series of SECOND GENERATION hardened power MOSFETs of both N and P channel enhancement types with ratings from 100V to 500V, 1A to 60A, and on resistance as low as 25mΩ. Total dose hardness is offered at 100K RAD(Si) and 1000KRAD(Si) with neutron hardness ranging from 1E13n/cm<sup>2</sup> for 500V product to 1E14n/cm<sup>2</sup> for 100V product. Dose rate hardness (GAMMA DOT) exists for rates to 1E9 without current limiting and 2E12 with current limiting.

This MOSFET is an enhancement-mode silicon-gate power field effect transistor of the vertical DMOS (VDMOS) structure. It is specially designed and processed to exhibit minimal characteristic changes to total dose (GAMMA) and neutron (n<sup>0</sup>) exposures. Design and processing efforts are also directed to enhance survival to heavy ion (SEE) and/or dose rate (GAMMA DOT) exposure.

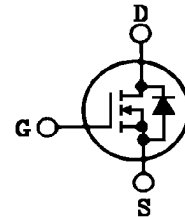
This part may be supplied as a die or in various packages other than shown above. Reliability screening is available as either non TX (commercial), TX equivalent of MIL-S-19500, TXV equivalent of MIL-S-19500, or space equivalent of MIL-S-19500. Contact the Harris Semiconductor High-Reliability Marketing group for any desired deviations from the data sheet.

## Package

TO-205AF



## Symbol



## Absolute Maximum Ratings (TC = +25°C) Unless Otherwise Specified

	FRL130D, R, H	UNITS
Drain-Source Voltage . . . . .	100	V
Drain-Gate Voltage (RGS = 20kΩ) . . . . .	100	V
Continuous Drain Current		
TC = +25°C . . . . .	8	A
TC = +100°C . . . . .	5	A
Pulsed Drain Current . . . . .	24	A
Gate-Source Voltage . . . . .	±20	V
Maximum Power Dissipation		
TC = +25°C . . . . .	25	W
TC = +100°C . . . . .	10	W
Derated Above +25°C . . . . .	0.20	W/°C
Inductive Current, Clamped, L = 100μH, (See Test Figure) . . . . .	24	A
Continuous Source Current (Body Diode) . . . . .	8	A
Pulsed Source Current (Body Diode) . . . . .	24	A
Operating And Storage Temperature . . . . .	-55 to +150	°C
Lead Temperature (During Soldering)		
Distance > 0.063 in. (1.6mm) From Case, 10s Max. . . . .	300	°C

CAUTION: These devices are sensitive to electrostatic discharge. Users should follow proper IC Handling Procedures.

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File Number **3218.1**

## FRL130D, FRL130R, FRL130H

### Pre-Radiation Electrical Specifications TC = +25°C, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS		UNITS
			MIN	MAX	
Drain-Source Breakdown Volts	BVDSS	VGS = 0, ID = 1mA	100	-	V
Gate-Threshold Volts	VGS(th)	VDS = VGS, ID = 1mA	2.0	4.0	V
Gate-Body Leakage Forward	IGSSF	VGS = +20V	-	100	nA
Gate-Body Leakage Reverse	IGSSR	VGS = -20V	-	100	nA
Zero-Gate Voltage Drain Current	IDSS1	VDS = 100V, VGS = 0	-	1	mA
	IDSS2	VDS = 80V, VGS = 0	-	0.025	
	IDSS3	VDS = 80V, VGS = 0, TC = +125°C	-	0.25	
Rated Avalanche Current	IAR	Time = 20μs	-	24	A
Drain-Source On-State Volts	VDS(on)	VGS = 10V, ID = 8A	-	1.51	V
Drain-Source On Resistance	RDS(on)	VGS = 10V, ID = 5A	-	.180	Ω
Turn-On Delay Time	td(on)	VDD = 50V, ID = 8A	-	35	ns
Rise Time	tr	Pulse Width = 3μs	-	210	
Turn-Off Delay Time	td(off)	Period = 300μs, Rg = 25Ω	-	200	
Fall Time	tf	0 ≤ VGS ≤ 10 (See Test Circuit)	-	145	
Gate-Charge Threshold	QG(th)	VDD = 50V, ID = 8A IGS1 = IGS2 0 ≤ VGS ≤ 20	1	4	nc
Gate-Charge On State	QG(on)		19	76	
Gate-Charge Total	QGM		35	142	
Plateau Voltage	VGP		3	12	V
Gate-Charge Source	QGS		3	13	nc
Gate-Charge Drain	QGD		9	38	
Diode Forward Voltage	VSD		ID = 8A, VGD = 0	0.6	1.8
Reverse Recovery Time	TT	I = 8A; di/dt = 100A/μs	-	450	ns
Junction-To-Case	Rθjc		-	5.0	°C/W
Junction-To-Ambient	Rθja	Free Air Operation	-	175	

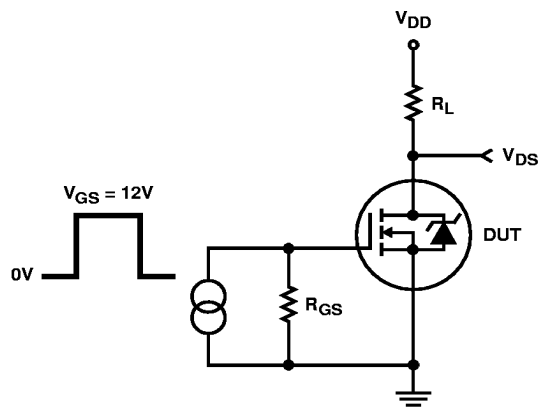


FIGURE 1. RESISTIVE SWITCHING TEST CIRCUIT

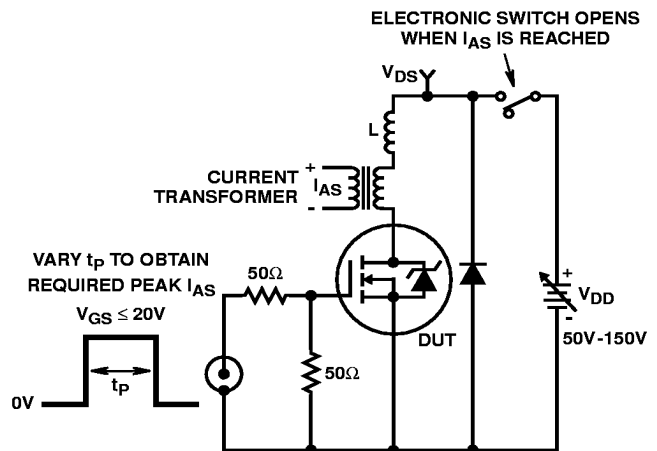


FIGURE 2. UNCLAMPED ENERGY TEST CIRCUIT

## FRL130D, FRL130R, FRL130H

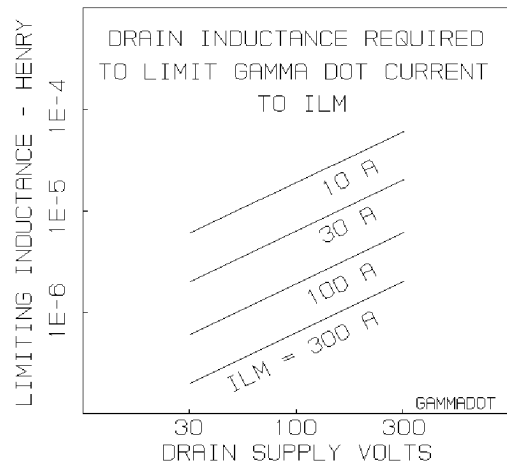
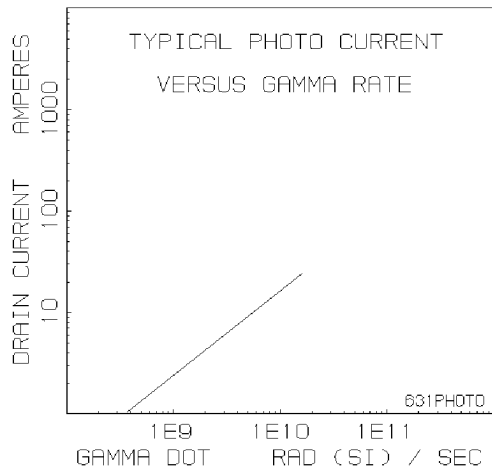
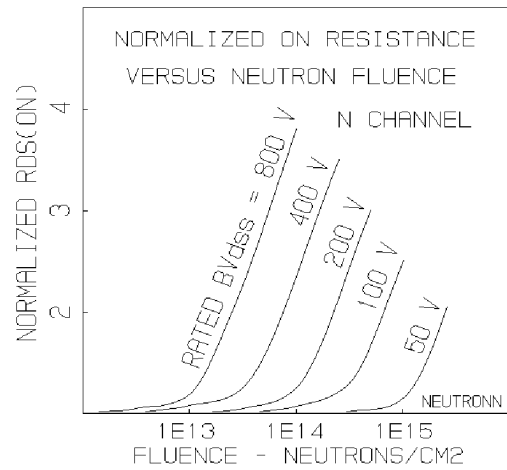
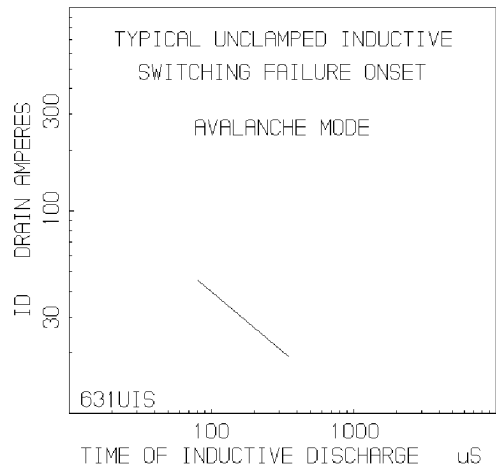
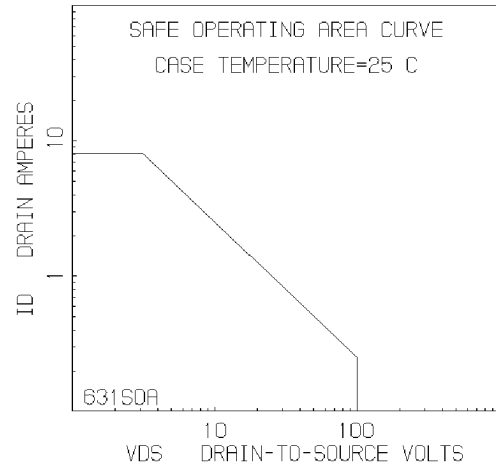
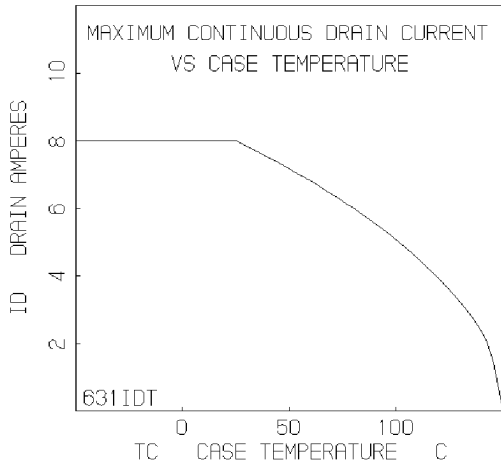
### Post-Radiation Electrical Specifications TC = +25°C, Unless Otherwise Specified

PARAMETER	SYMBOL	TYPE	TEST CONDITIONS	LIMITS		UNITS	
				MIN	MAX		
Drain-Source Breakdown Volts	(Note 4, 6)	BVDSS	FRL130D, R	VGS = 0, ID = 1mA	100	-	V
	(Note 5, 6)	BVDSS	FRL130H	VGS = 0, ID = 1mA	95	-	V
Gate-Source Threshold Volts	(Note 4, 6)	VGS(th)	FRL130D, R	VGS = VDS, ID = 1mA	2.0	4.0	V
	(Note 3, 5, 6)	VGS(th)	FRL130H	VGS = VDS, ID = 1mA	1.5	4.5	V
Gate-Body Leakage Forward	(Note 4, 6)	IGSSF	FRL130D, R	VGS = 20V, VDS = 0	-	100	nA
	(Note 5, 6)	IGSSF	FRL130H	VGS = 20V, VDS = 0	-	200	nA
Gate-Body Leakage Reverse	(Note 2, 4, 6)	IGSSR	FRL130D, R	VGS = -20V, VDS = 0	-	100	nA
	(Note 2, 5, 6)	IGSSR	FRL130H	VGS = -20V, VDS = 0	-	200	nA
Zero-Gate Voltage Drain Current	(Note 4, 6)	IDSS	FRL130D, R	VGS = 0, VDS = 80V	-	25	μA
	(Note 5, 6)	IDSS	FRL130H	VGS = 0, VDS = 80V	-	100	μA
Drain-Source On-State Volts	(Note 1, 4, 6)	VDS(on)	FRL130D, R	VGS = 10V, ID = 8A	-	1.51	V
	(Note 1, 5, 6)	VDS(on)	FRL130H	VGS = 16V, ID = 8A	-	2.27	V
Drain-Source On Resistance	(Note 1, 4, 6)	RDS(on)	FRL130D, R	VGS = 10V, ID = 5A	-	0.180	Ω
	(Note 1, 5, 6)	RDS(on)	FRL130H	VGS = 14V, ID = 5A	-	0.270	Ω

**NOTES:**

1. Pulse test, 300μs max
2. Absolute value
3. Gamma = 300KRAD(Si)
4. Gamma = 10KRAD(Si) for "D", 100KRAD(Si) for "R". Neutron = 3E13
5. Gamma = 1000KRAD(Si). Neutron = 3E13
6. Insitu Gamma bias must be sampled for both VGS = +10V, VDS = 0V and VGS = 0V, VDS = 80% BVDSS
7. Gamma data taken 4/19/90 on TA 17631 devices by GE ASTRO SPACE; EMC/SURVIVABILITY LABORATORY; KING OF PRUSSIA, PA 19401
8. Single event drain burnout testing by Titus, J.L., et al of NWSC, Crane, IN at Brookhaven Nat. Lab. Dec 11-14, 1989
9. Neutron derivation, HARRIS Application note AN-8831, Oct. 1988

Typical Performance Characteristics



**Rad Hard Data Packages - Harris Power Transistors**

**TXV Equivalent**

**1. Rad Hard TXV Equivalent - Standard Data Package**

- A. Certificate of Compliance
- B. Assembly Flow Chart
- C. Preconditioning - Attributes Data Sheet
- D. Group A - Attributes Data Sheet
- E. Group B - Attributes Data Sheet
- F. Group C - Attributes Data Sheet
- G. Group D - Attributes Data Sheet

**2. Rad Hard TXV Equivalent - Optional Data Package**

- A. Certificate of Compliance
- B. Assembly Flow Chart
- C. Preconditioning - Attributes Data Sheet  
- Precondition Lot Traveler  
- Pre and Post Burn-In Read and Record Data
- D. Group A - Attributes Data Sheet  
- Group A Lot Traveler
- E. Group B - Attributes Data Sheet  
- Group B Lot Traveler  
- Pre and Post Read and Record Data for Intermittent Operating Life (Subgroup B3)  
- Bond Strength Data (Subgroup B3)  
- Pre and Post High Temperature Operating Life Read and Record Data (Subgroup B6)
- F. Group C - Attributes Data Sheet  
- Group C Lot Traveler  
- Pre and Post Read and Record Data for Intermittent Operating Life (Subgroup C6)  
- Bond Strength Data (Subgroup C6)
- G. Group D - Attributes Data Sheet  
- Group D Lot Traveler  
- Pre and Post RAD Read and Record Data

**Class S - Equivalents**

**1. Rad Hard "S" Equivalent - Standard Data Package**

- A. Certificate of Compliance
- B. Serialization Records
- C. Assembly Flow Chart
- D. SEM Photos and Report

- E. Preconditioning Attributes Data Sheet  
Hi-Rel Lot Traveler  
HTRB - Hi Temp Gate Stress Post Reverse Bias Data and Delta Data  
HTRB - Hi Temp Drain Stress Post Reverse Bias Delta Data
- F. Group A - Attributes Data Sheet
- G. Group B - Attributes Data Sheet
- H. Group C - Attributes Data Sheet
- I. Group D - Attributes Data Sheet

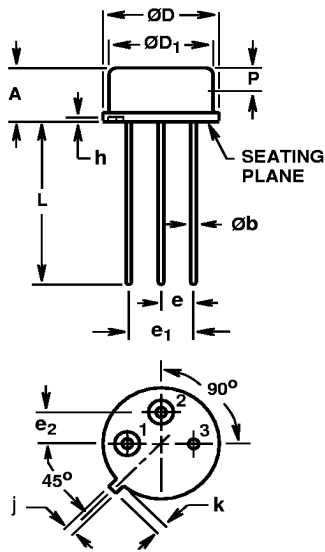
**2. Rad Hard Max. "S" Equivalent - Optional Data Package**

- A. Certificate of Compliance
- B. Serialization Records
- C. Assembly Flow Chart
- D. SEM Photos and Report
- E. Preconditioning - Attributes Data Sheet  
- Hi-Rel Lot Traveler  
- HTRB - Hi Temp Gate Stress Post Reverse Bias Data and Delta Data  
- HTRB - Hi Temp Drain Stress Post Reverse Bias Delta Data  
- X-Ray and X-Ray Report
- F. Group A - Attributes Data Sheet  
- Hi-Rel Lot Traveler  
- Subgroups A2, A3, A4, A5 and A7 Data
- G. Group B - Attributes Data Sheet  
- Hi-Rel Lot Traveler  
- Subgroups B1, B3, B4, B5 and B6 Data
- H. Group C - Attributes Data Sheet  
- Hi-Rel Lot Traveler  
- Subgroups C1, C2, C3 and C6 Data
- I. Group D - Attributes Data Sheet  
- Hi-Rel Lot Traveler  
- Pre and Post Radiation Data

FRL130D, FRL130R, FRL130H

**TO-205AF**

3 LEAD JEDEC TO-205AF HERMETIC METAL CAN PACKAGE



SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.160	0.180	4.07	4.57	-
Øb	0.016	0.021	0.41	0.53	2, 3
ØD	0.350	0.370	8.89	9.39	-
ØD <sub>1</sub>	0.315	0.335	8.01	8.50	-
e	0.095	0.105	2.42	2.66	4
e <sub>1</sub>	0.190	0.210	4.83	5.33	4
e <sub>2</sub>	0.095	0.105	2.42	2.66	4
h	0.010	0.020	0.26	0.50	-
j	0.028	0.034	0.72	0.86	-
k	0.029	0.045	0.74	1.14	-
L	0.500	0.560	12.70	14.22	3
P	0.075	-	1.91	-	5

NOTES:

1. These dimensions are within allowable dimensions of Rev. E of JEDEC TO-205AF outline dated 11-82.
2. Lead dimension (without solder).
3. Solder coating may vary along lead length, add typically 0.002 inches (0.05mm) for solder coating.
4. Position of lead to be measured 0.100 inches (2.54mm) from bottom of seating plane.
5. This zone controlled for automatic handling. The variation in actual diameter within this zone shall not exceed 0.010 inches (0.254mm).
6. Lead no. 3 butt welded to stem base.
7. Controlling dimension: Inch.
8. Revision 3 dated 6-94.